

Diode – Power, Bare Die

**Gen VII, Fast Recovery
 1200 V, 100 A**

PCFF100H120SWF

Features

- Advanced Gen VII Technology
- Fast and Soft Recovery
- Maximum Junction Temperature 175°C
- Low Forward Voltage: $V_F = 1.78\text{ V (Typ.) @ } I_F = 100\text{ A}$
- Easy to Parallel Operation

Typical Applications

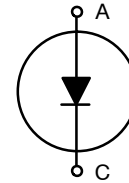
- Solar
- Energy storage
- Industrial motor control

MECHANICAL PARAMETERS

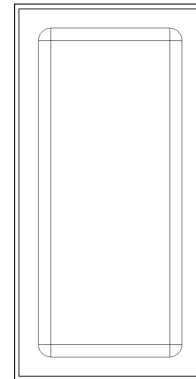
Parameter	Value	Unit
Die Size (w/ Scribe Lane)	4,200 x 8,400	μm^2
Anode Pad Size	3,237 x 7,437	μm^2
Scribe Lane Width	80	μm
Die Thickness	119	μm
Top Metal	6 μm AlSiCu	
Back Metal	1.65 μm Ti/NiV/Ag	
Topside Passivation	Silicon Nitride plus Polyimide	
Wafer Diameter	200 mm	
Max Possible Die Per Wafer	686	
Recommended Storage Environment	In original container, in dry nitrogen, < 6 months at an ambient temperature of 23°C	

$V_R = 1200\text{ V}$
 $I_F = 100\text{ A}$

DIODE DIE



DIE OUTLINE



ORDERING INFORMATION

Device	Inking	Shipping
PCFF100H120SWF	Yes	Sawn Wafer on Tape

PCFF100H120SWF

ABSOLUTE MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Ratings	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	1200	V
DC Forward Current, limited by $T_{J\max}$ (Note 1)	I_F	100	A
Pulsed Forward Current, t_p limited by $T_{J\max}$ (Note 2)	I_{FM}	300	A
Operating Junction Temperature	T_J	-40 to +175	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	+18 to +28	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- Nominal forward current at $T_c = 100^\circ\text{C}$ when assembled in power module
- Not subject to production test – verified by design/characterization.

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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STATIC CHARACTERISTICS (Tested on Wafers)

Breakdown Voltage	V_{BR}	$I_R = 1\text{ mA}$	1200	–	–	V
Reverse Leakage Current	I_R	$V_R = 1200\text{ V}$	–	–	10	μA
Forward Voltage	V_F	$I_F = 100\text{ A}$	–	1.78	2.08	V

ELECTRICAL CHARACTERISTICS (Not subjected to production test – verified by design/characterization)

Breakdown Voltage	V_{BR}	$I_R = 1\text{ mA}$	$T_J = -40^\circ\text{C}$	1200	–	–	V
Forward Voltage	V_F	$I_F = 100\text{ A}$	$T_J = 175^\circ\text{C}$	–	1.9	–	V
Reverse Recovery Time	T_{rr}	$I_F = 100\text{ A}, V_R = 600\text{ V},$ $di_F/dt = 500\text{ A}/\mu\text{s}, T_J = 25^\circ\text{C}$		–	347.1	–	nS
Reverse Recovery Charge	Q_{rr}			–	4.4	–	μC
Reverse Recovery Current	I_{RRM}			–	25.8	–	A
Reverse Recovery Time	T_{rr}	$I_F = 100\text{ A}, V_R = 600\text{ V},$ $di_F/dt = 500\text{ A}/\mu\text{s}, T_J = 175^\circ\text{C}$		–	572.2	–	nS
Reverse Recovery Charge	Q_{rr}			–	12.5	–	μC
Reverse Recovery Current	I_{RRM}			–	43.6	–	A

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

NOTE: Switching characteristics and thermal properties are depending strongly on module design and mounting technology.

PCFF100H120SWF

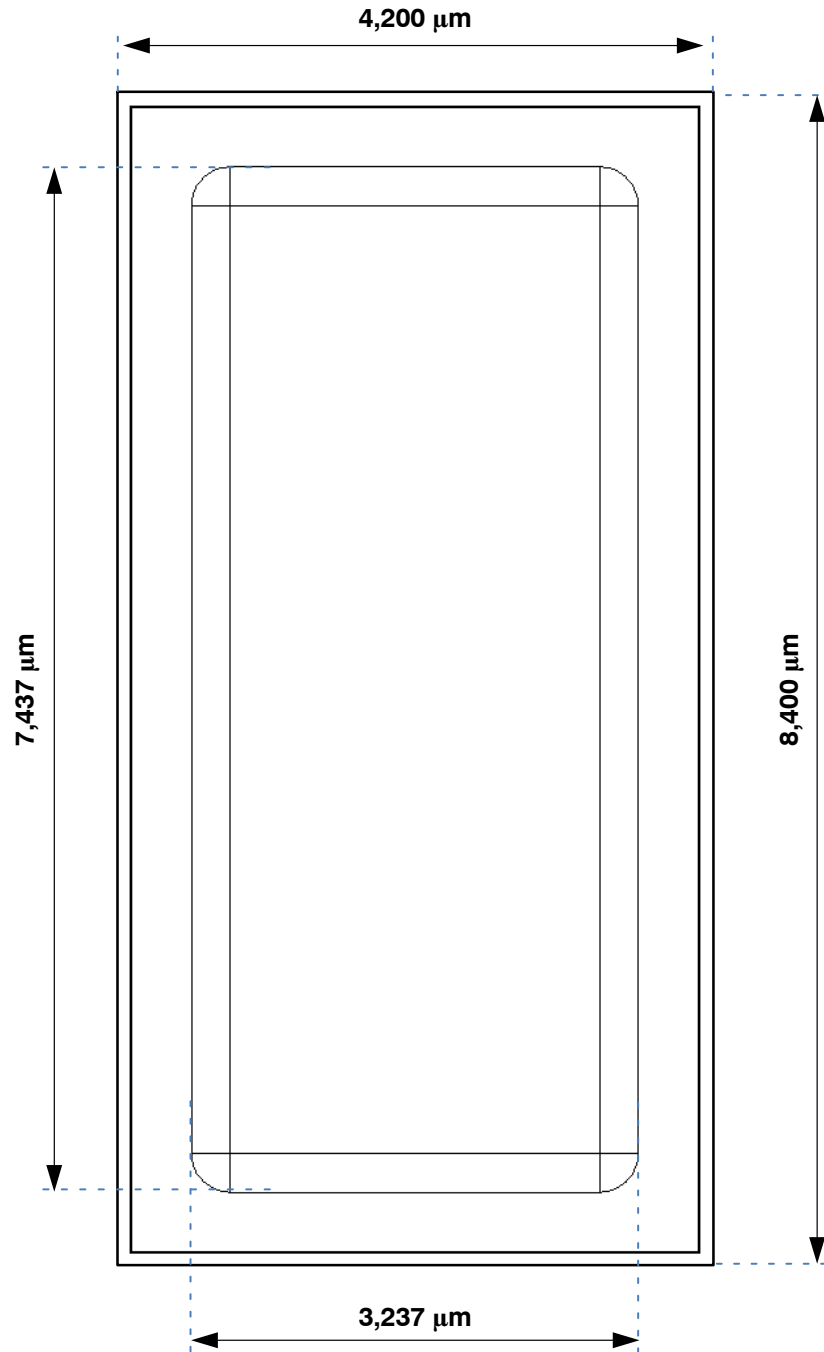


Figure 1. Die Layout

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